

## Studies on compensating valency substituted $\text{BaTi}_{(1-x)}\text{Mn}_{x/2}\text{Nb}_{x/2}\text{O}_3$ ceramics

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**Abstract.** The paper reports investigations of relative permittivity,  $\epsilon_r$ , electrical conductivity,  $\sigma$ , saturation polarization,  $P_s$ , infrared absorption and structural properties of compensating valency substituted  $\text{BaTiO}_3$ . The compositions investigated are  $\text{BaTi}_{(1-x)}\text{Mn}_{x/2}\text{Nb}_{x/2}\text{O}_3$  for  $x = 0.00; 0.025; 0.05; 0.1; 0.2; 0.4$ . The compositions for  $x < 0.1$  are observed to be ferroelectric and the transition temperature and value of  $\epsilon_r$  are observed to decrease as concentration of substitution is increased. The dielectric investigations are carried out on two sets of samples (i) as sintered and (ii) annealed. Annealing is observed to improve quality factor ' $Q$ ' of the materials with a consequent reduction in the  $\epsilon_r$ . The observations on  $\epsilon_r$  and saturation polarization suggest that additional material engineering efforts are required to improve the material properties.

**Keywords.** Valence compensating ceramic; barium titanate; dielectric constant; electron-transport properties; saturation polarization.

### 1. Introduction

It has been observed that the relaxors in the ceramic form could be stabilized in the perovskite crystal structure only if they are combined with a certain amount of displacer ferroelectrics like  $\text{PbTiO}_3$ ,  $\text{BaTiO}_3$  (Agrawal 1997). The relaxors are known for their high dielectric constant and piezoelectric coupling coefficient; but the relaxors are found to possess very low  $Q$  as a consequence of occurrence of infra-grain space charge layers.

Further the  $\text{BaTiO}_3$  having its high  $\epsilon_r$ , low coercive field and moderately high curie temperature is an important dielectric material for piezoelectric and pyroelectric application. Nevertheless the literature survey indicates that  $\text{BaTiO}_3$  is less intensively investigated for the effect of compensating off valency substitution as compared to PT and PZT materials. One of the possible reasons could be the observation that the compensating off valency substitution depresses the curie point drastically (Nakamura and Nomura 1966). For example, the substitution of 2 Ti by a Fe or a Ta depresses the curie point below  $0^\circ\text{C}$  for 10 atom% level of substitution. Taking into consideration the points above, it appears that, the  $\text{BaTiO}_3$  may exhibit interesting changes in properties for very low levels of off valency substitution, and therefore we have investigated the system as given here:  $\text{BaTi}_{(1-x)}\text{Mn}_{x/2}\text{Nb}_{x/2}\text{O}_3$  for  $x = 0.00; 0.025; 0.05; 0.1; 0.2; 0.4$ . (It was expected that the interesting behavioural changes may occur for  $x < 0.1$ ).

### 2. Experimental

The systems under investigation were synthesized via standard ceramic route. The respective oxides of purity 99.9% were mixed, ground, pelletized and subjected to presintering for 24 h at  $1180^\circ\text{C}$ . The effect of sintering schedule on the properties of pure and donor doped  $\text{BaTiO}_3$  is well reported (Heydrich 1976; Bi-Shiou *et al* 1987). Also Mn prefers to be in state +3 for  $530^\circ\text{C} < T < 940^\circ\text{C}$  (Dean 1987). Applying a qualitative logic the sintering schedule was selected so as to stabilize Mn in state +3. Further,  $1280^\circ\text{C}$  was selected as final sintering temperature. The final sintering was carried out for 6 h. At high temperature the system under investigation was expected to lose traces of oxygen (Shail Upadya *et al* 1996). Reoxidation may take place if the samples are annealed at temperature below  $1200^\circ\text{C}$  for a long time. Additionally annealing may reduce thermal stresses also and may lead to an improvement in quality factor of the material (Scenger *et al* 1979; Setter *et al* 1980). To investigate this effect qualitatively we have prepared two sets of samples.

#### 2.1 Sintered

In this case after sintering at  $1280^\circ\text{C}$  the samples were allowed to cool in the tubular furnace with its natural cooling rate of  $10^\circ\text{C}/\text{min}$  up to temperature below  $900^\circ\text{C}$ .

#### 2.2 Annealed

The sintered compounds were reheated and maintained at  $1150^\circ\text{C}$  for 6 h and cooled below  $900^\circ\text{C}$  at the rate of

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The samples were subjected to investigations using Philips PW 1710 X-ray diffractometer. The infrared absorption properties were measured using Perkin-Elmer IR spectrometer. To measure the dielectric dispersion a HP-4284 A impedance bridge was used. The saturation polarization,  $P_s$  was measured using a circuit similar to the one reported earlier (Sinha 1965). The observations were taken up at an interval of 2°C, though the figures of  $\epsilon_r$ ,  $P_s$  indicate only a few representative points amongst these.

### 3. Results and discussion

#### 3.1 XRD

The XRD was carried out using the JCPD standard data on BaTiO<sub>3</sub> and simultaneously using the graphical technique (Hull and Davey 1921; Cullity 1978). The XRD shows a tetragonal structure and observed  $a$ ,  $c$ ,  $c/a$  are shown in table 1.  $c/a$  is observed to be 1.01 for all the samples. The values of  $a$  and  $c$  are also constant within the error limits of statistical averaging. The values are observed to be equal to the  $a$ ,  $c$ ,  $c/a$  for pure BaTiO<sub>3</sub> prepared in the same sintering schedule. Thus the structure parameters are independent of  $x$  as expected on the basis of relative ionic sizes of Nb (0.70 AU), Mn (0.74 AU) and Ti (0.68 AU).

#### 3.2 Infrared absorption

In case of BaTiO<sub>3</sub>, the absorption at infrared frequencies has been extensively used to probe the interatomic forces and the investigations are more useful to probe the interaction between the Ti and O ions in the octahedral geometry, the TiO<sub>6</sub> octahedron (Mara 1954; Last 1956).

In the system under investigation, the Ti site in ABO<sub>3</sub> crystal structure is being modified. Further, it is also well accepted that the displacement of the Ti ions from its centre caused ferroelectricity in these materials. Therefore investigations of the infrared absorption is expected to reveal a valuable information about the modification

caused in the interatomic forces between Ti and O<sub>6</sub> ions to the substitution.

Figure 1 shows the IR absorption spectra for  $x = 0.05$  and the overall nature of the absorption spectra for all the levels of substitution studied is similar to spectrum for  $x = 0.05$ . Two absorption bands are observed in the frequency range 200–1000 cm<sup>-1</sup>. The absorption band at higher frequency is labelled as  $n_1$  while the one at lower frequency is labelled as  $n_2$ . The band  $n_1$  is more asymmetric as compared to the one at  $n_2$  and the present observations are in confirmation with the observations reported by Last (1956). The values of  $n_1$ ,  $n_2$ ,  $k_s$  and  $k_b$  for varying concentrations are shown in table 2, where  $k_s$  and  $k_b$  are the force constants for stretching and bending modes of vibrations respectively. The values of  $n_1$  and  $n_2$  for  $x = 0$  are also equal to the reported values (Mara 1954; Last 1956). It has been observed that as the value of  $x$  increases the absorption band at  $n_1$  becomes more asymmetric and broadened. For  $x = 0.2$  and  $x = 0.4$  the shoulders are observed in the  $n_1$  band which are characteristic of further lowered symmetry (Last 1956).

The absorption bands at  $n_1$  and  $n_2$  could be associated to the stretching and bending modes of vibrations of TiO<sub>6</sub> octahedron (Last 1956) and the corresponding force con-

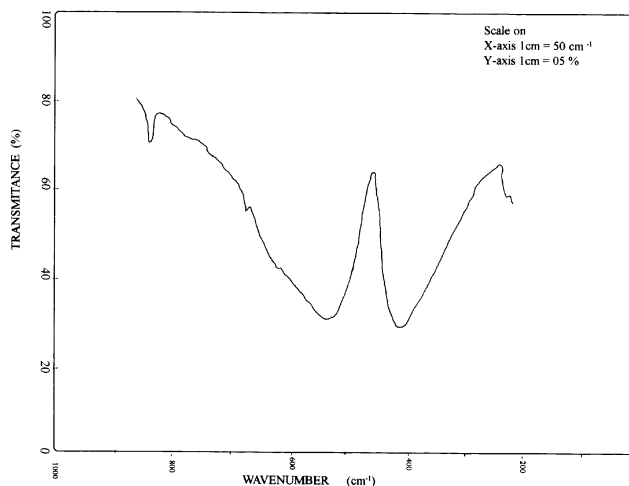


Figure 1. The infrared absorption spectra of BaTi<sub>0.95</sub>Nb<sub>0.025</sub>Mn<sub>0.025</sub>O<sub>3</sub>.

Table 1. Values of  $a$ ,  $c$  and  $c/a$  for BaTi<sub>(1-x)</sub>Mn<sub>x/2</sub>Nb<sub>x/2</sub>O<sub>3</sub>.

$X$	$a$	$c$	$c/a$
0.000	3.989	4.029	1.01
0.025	3.991	4.041	1.01
0.050	3.994	4.034	1.01
0.100	3.992	4.032	1.01
0.200	3.994	4.034	1.01
0.400	3.983	4.024	1.01

Table 2. Values of  $g_1$ ,  $g_2$ ,  $K_s$ ,  $K_b$  for BaTi<sub>(1-x)</sub>Mn<sub>x/2</sub>Nb<sub>x/2</sub>O<sub>3</sub>.

$X$	$g_1$	$g_2$	$K_s$	$K_b$
0.000	540	400	$0.920 \times 10^5$	$0.680 \times 10^5$ as reported
0.000	545	400	$0.798 \times 10^5$	$0.638 \times 10^5$ as reported
0.050	535	395	$0.880 \times 10^5$	$0.740 \times 10^5$
0.200	550	375	$1.040 \times 10^5$	$0.550 \times 10^5$
0.400	560	360	$1.040 \times 10^5$	$0.490 \times 10^5$

stant could be calculated using standard procedure of solving the secular equations.

$$\begin{vmatrix} (m_0 + m_1)2k_s - I & m_0(4k_b) \\ -m_0(2k_s) & (m_0 + m_1)4k_b - I \end{vmatrix} = 0,$$

where  $m_0$  and  $m_1$  are the reciprocal masses of Ti and O ions, respectively.

It is observed that  $n_2$  and  $k_b$  decreases as the level of substitution is increased while  $n_1$  and  $k_s$  increases with the increasing level of substitution. The force constant,  $k_s$ , in this case is related to change in the bond length of  $\text{O}_I\text{-Ti-O}_I$  ions along the polar axis. Therefore increasing values of  $n_1$  correlate to increasing asymmetry in the  $\text{O}_{II}\text{-Ti-O}_{II}$  bond. As  $c$  is observed independent of concentration, this increased asymmetry may lead to an increase in the asymmetry of  $\text{O}_I\text{-Ti-O}_I$  ions.

From the basic theory of infrared oscillations (Hertzberg 1945), the force constant  $k_b$  is inversely proportional to the displacement of Ti (or NbMn pair) from its centre

in  $\text{TiO}_6$  octahedron. Now as increasing  $k_s$  leads to increasing asymmetry same phenomenon should lead to increasing displacement and decreasing  $k_b$  and  $n_2$ .

### 3.3 Dielectric constant

Figures 2 and 3 show the relative permittivity  $\epsilon_r$  as a function of temperature for the sintered (S) and annealed (A) samples. The general observations are as follows.

(I) The system for  $x < 0.1$  is ferroelectric at room temperature. Therefore the behaviour of dielectric constant for  $x = 0.2$  and  $x = 0.4$  are not shown in the figure.

(II) The value of  $\epsilon_r$  for S-type sample is more than that for A-type sample and  $Q(A) > Q(S)$ .

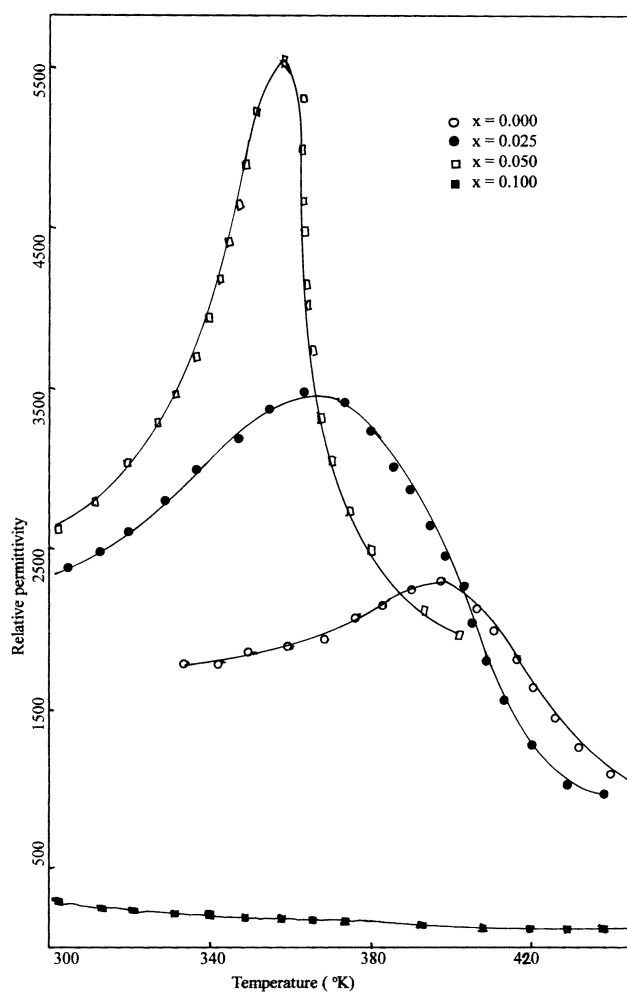
(III) The peak is observed in the  $\epsilon_r$  vs  $T$  behaviour and it is a diffused one.

(IV)  $T_c$  appears decreasing as the substitution  $x$  is increased. The  $\epsilon_{r\text{max}}$  initially increases and then decreases with  $x$  leading to non-ferroelectric compositions (table 3).

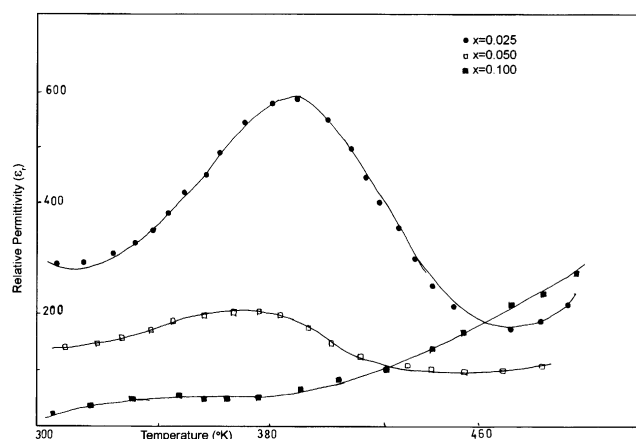
(V) The relative permittivity vs temperature behaviour for  $x = 0$  is observed on the similar lines as reported earlier (Flores-Ramirez *et al* 1989) and the  $T_c$  is observed at  $120^\circ\text{C}$ . It is important to note that the behaviour of  $\epsilon_r$  vs temperature is sensitive to the sintering temperature. As the sintering temperature used is  $1280^\circ\text{C}$  the  $\epsilon_r$  vs  $T$  behaviour is expected to show a broad rather than a sharp peak.

The observations  $\epsilon_r(S) > \epsilon_r(A)$  and  $Q(A) > Q(S)$  show that the total impedance of the material is increased as the samples are annealed (about 2 times for  $x = 0.025$  and  $0.05$ ). Further, corollaries of this observation are as follows.

Now the materials being investigated are displacer substituted relaxors and the annealing is expected to homogenize the material and reduce thermal stress. The relaxors are believed to possess microchemical inhomogeneity and corresponding space charge regions are



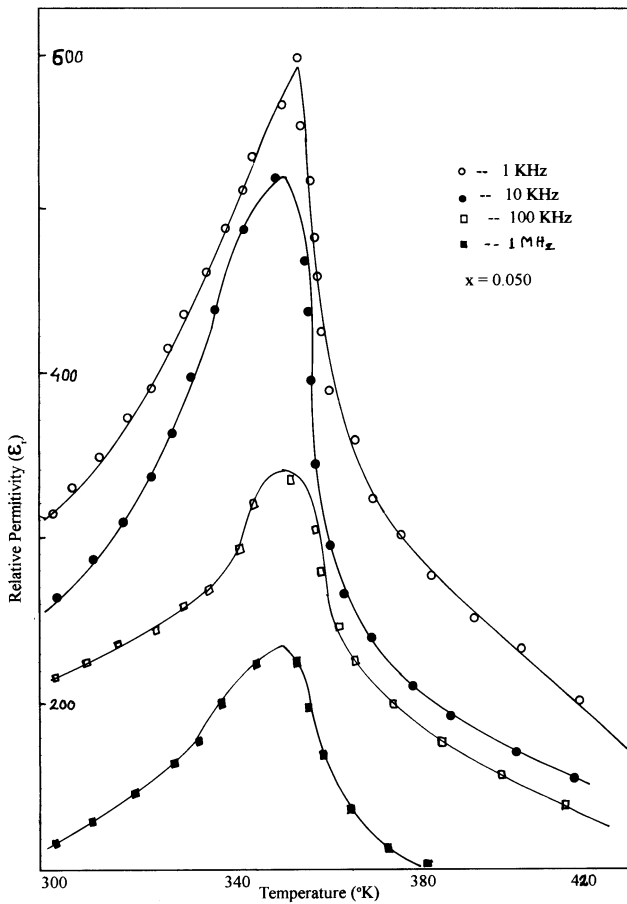
**Figure 2.** Variation of relative permittivity  $\epsilon_r$  with temperature for  $\text{BaTi}_{(1-x)}\text{Nb}_{x/2}\text{Mn}_{x/2}\text{O}_3$  (sintered).



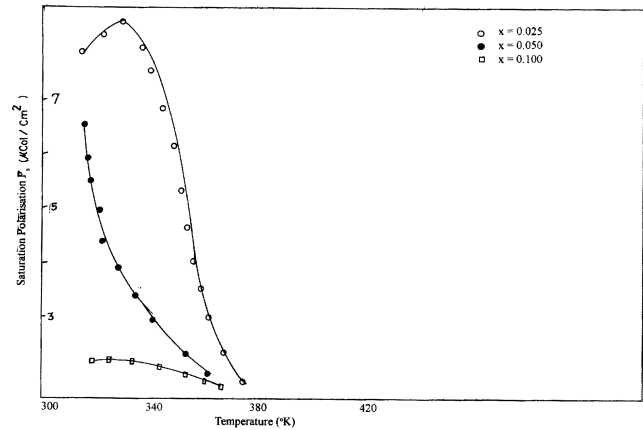
**Figure 3.** Variation of relative permittivity with temperature for  $\text{BaTi}_{(1-x)}\text{Nb}_{x/2}\text{Mn}_{x/2}\text{O}_3$  (annealed).

**Table 3.** Values of  $e_{rmax}$ ,  $e_{RT}$ ,  $T_c$ ,  $Q_{RT}$  and  $t$  for  $BaTi_{(1-x)}Mn_{x/2}Nb_{x/2}O_3$ .

X	As sintered					Annealed				
	$T_c$	$e_{rmax} (-/+5)$	$e_{rRT} (-/+5)$	$Q_{RT}$	$t$	$T_c$	$e_{rmax}$	$e_{rRT}$	$Q_{RT}$	$t$
0.000	395	2400	1700	1.22	—	390	280	190	13.9	—
0.025	372	3600	1800	1.57	0.85	388	600	285	13.18	0.97
0.050	365	5700	2000	1.19	0.75	378	210	130	2.32	0.91
0.100	303	280	280	2.08	0.61	~ 303	56	025	3.80	—

**Figure 4.** Variation of relative permittivity with temperature for different frequencies of  $BaTi_{(1-x)}Mn_{x/2}Nb_{x/2}O_3$  for annealed.

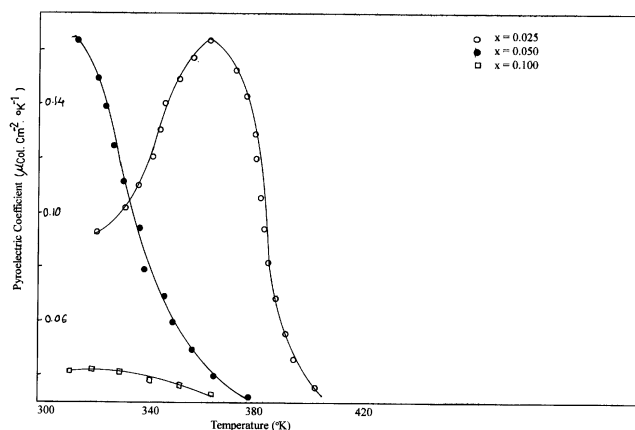
responsible for the high value of their dielectric constant (Agrawal 1997). The material under investigation could be a partially relaxor material. It is reported for the relaxors that the annealing of the material leads to an ordered state, where the dielectric constant is reduced and  $Q$  increased (Scenger *et al* 1979; Setter and Cross 1980). Therefore the present observations of reduced  $e_r$  and increased  $Q$  for annealed samples indicate that the materials under investigation are at least partially relaxors. The behaviour of  $e_r$  in the paraelectric region has been fitted to an equation

**Figure 5.** Variation of saturation polarization  $P_s$  with temperature for  $BaTi_{(1-x)}Nb_{x/2}Mn_{x/2}O_3$  (annealed).

$$e_r^{-1} = e_{rmax}^{-1} + A(T - T_c)^t,$$

where  $t = 1$  for displacer material and  $t = 2$  for the relaxor (Pandey *et al* 1997).

It has been observed that the  $Pb_xCa_{(1-x)}Ni_{y/2}W_{y/2}Ti_{(1-y)}O_3$  systems possess  $t$  between 1 and 2 (Prasad *et al* 1996).  $1 < t < 2$  is associated to partially relaxors nature of the material. The values of  $e_{rmax}$ ,  $e_r(A)$ ,  $e_r(S)$ ,  $Q(A)$ ,  $Q(S)$   $t$  for varying values of  $x$  are given in table 3. It is observed that  $t < 1$ . For NbMn systems the phase transition is a diffused one and has been associated with the chemical inhomogeneity within the grain. If the phase transition is a diffused one  $t$  may appear even less than 1 also and may not clearly indicate whether material is displacer or relaxor. To determine whether the material has at least partial relaxor behaviour, we have measured the  $e_r$  as a function of both temperature and frequency. Figure 4 shows  $e_r$  as function of both temperature and frequency for  $x = 0.05$ . From figure 4 it is apparent that the  $T_c$  increases slightly as frequency is increased. This observation has confirmed the relaxor contribution to the material. Another important feature of the measurement is that the  $BaTiO_3$  at 1 KHz show that the  $e_r$  increases with temperature in the paraelectric region. This behaviour is ascribed to the polycrystallinity of the material (Flores-Ramirez *et al* 1989).



**Figure 6.** Variation of pyroelectric coefficient with temperature for  $\text{BaTi}_{(1-x)}\text{Nb}_{x/2}\text{Mn}_{x/2}\text{O}_3$  (annealed).

### 3.4 Saturation polarization

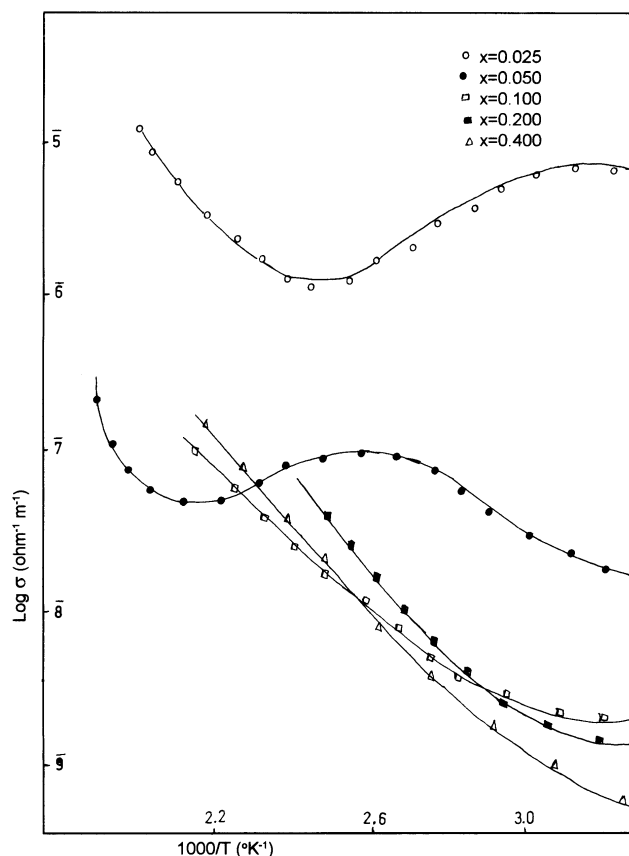
The ceramic samples have inherent porosity and reduced dielectric strength. Therefore we have used maximum electrical field of 3.5–4 kV/cm. The observed loops are typical of polycrystalline material (Bera and Choudhary 1997). The behaviour of  $P_s$  vs temperature is shown in figure 5. The saturation polarization,  $P_s$  decreases as the level of substitution is increased and the  $P_s$  vs  $T$  behaviour shows a smear in the phase transition region typical of the DPT (Jun Kawata *et al* 1982). It is interesting to note that the  $P_s$  increases slightly near room temperature. This could be due to a smear in  $P_s$  due to orthorhombic to tetragonal phase transition, expected near 0°C from the investigation on substituted  $\text{BaTiO}_3$ . The observed saturation polarization shows that as  $x$  is increased the material tends to be non-ferroelectric for  $x = 0.025$  ( $\sim 7 \mu\text{Coul}/\text{cm}^2$ ) and is within the range that is reported for pure ceramic  $\text{BaTiO}_3$ . Using the  $P_s$  as  $T$  behaviour we have calculated the pyroelectric coefficient  $g$  as shown in figure 6. The  $g$  is also observed to decrease as  $x$  is increased.

### 3.5 Conductivity

The measurement of conductivity (figure 7) also shows a behaviour similar to the PTCR effect (Pandey *et al* 1997) near curie point, but the resistivity is observed to be sufficiently high at  $\sim 10^{-6}$  ohm m, both above and below the curie point. To explain such a behaviour a refined two level model is essential (Pandey *et al* 1997). Few observations are noteworthy.

(I) The very high values of the resistivity for all the observations suggest that the Mn is stabilized in oxidation state + 3.

(II) The conductivity is observed to decrease with  $T$  slowly in the PTCR region and the effect is a diffused one rather than being a sharp transition as in case of



**Figure 7.** Variation of  $\log s$  with  $1000/T$  for  $\text{BaTi}_{(1-x)}\text{Nb}_{x/2}\text{Mn}_{x/2}\text{O}_3$  (annealed).

donor doped  $\text{BaTiO}_3$ . In case of donor doped  $\text{BaTiO}_3$  Hewang's model predicts a barrier layer at grain boundary, where the barrier potential is proportional to  $1/e$ . For the samples under investigation the phase transition is diffused and  $e$  decreases in a diffused manner with  $T$  in paraelectric region. This may lead to diffused PTCR effect.

(III)  $e_{\text{max}}$  reduces with  $x$  and also the  $\log s$  decreases with  $x$ . This feature could be correlated at least qualitatively on the basis of the Hawang's model.

## 4. Conclusion

The substitution of  $\text{Mn}_{1/2}\text{Nb}_{1/2}$  for a Ti, in case of  $\text{BaTiO}_3$  suppresses the transition temperature ( $T_c$ ). For very low concentration of substitution the  $e_r$  is observed to increase owing to the added contribution of the space charge layers due to the microchemical inhomogeneity. The increased level of substitution leads to tetragonal but non-ferroelectric composition. The observations on  $e_r$  and saturation polarization suggest that the additional material engineering efforts are required to improve the material properties.

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